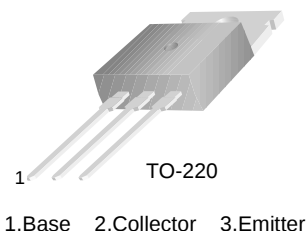


MJE13006/13007

High Voltage Switch Mode Application

- High Speed Switching
- Suitable for Switching Regulator and Motor Control



NPN Silicon Transistor

Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	: MJE13006	600 V
		: MJE13007	700 V
V_{CEO}	Collector-Emitter Voltage	: MJE13006	300 V
		: MJE13007	400 V
V_{EBO}	Emitter- Base Voltage	9	V
I_C	Collector Current (DC)	8	A
I_{CP}	Collector Current (Pulse)	16	A
I_B	Base Current	4	A
P_C	Collector Dissipation ($T_C=25^\circ\text{C}$)	80	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature	- 65 ~ 150	$^\circ\text{C}$

Electrical Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CEO}	Collector- Emitter Breakdown Voltage	$I_C = 10\text{mA}, I_B = 0$	300 400			V
						V
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 9\text{V}, I_C = 0$			1	mA
h_{FE}	*DC Current Gain	$V_{CE} = 5\text{V}, I_C = 2\text{A}$	8		60	
		$V_{CE} = 5\text{V}, I_C = 5\text{A}$	5		30	
$V_{CE(sat)}$	*Collector-Emitter Saturation Voltage	$I_C = 2\text{A}, I_B = 0.4\text{A}$			1	V
		$I_C = 5\text{A}, I_B = 1\text{A}$			2	V
		$I_C = 8\text{A}, I_B = 2\text{A}$			3	V
$V_{BE(sat)}$	*Base-Emitter Saturation Voltage	$I_C = 2\text{A}, I_B = 0.4\text{A}$			1.2	V
		$I_C = 5\text{A}, I_B = 1\text{A}$			1.6	V
C_{ob}	Output Capacitance	$V_{CB} = 10\text{V}, f = 0.1\text{MHz}$		110		pF
f_T	Current Gain Bandwidth Product	$V_{CE} = 10\text{V}, I_C = 0.5\text{A}$	4			MHz
t_{ON}	Turn ON Time	$V_{CC} = 125\text{V}, I_C = 5\text{A}$ $I_{B1} = -I_{B2} = 1\text{A}$ $R_L = 50\Omega$			1.6	μs
t_{STG}	Storage Time				3	μs
t_F	Fall Time				0.7	μs

* Pulse test: $PW \leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

Typical Characteristics

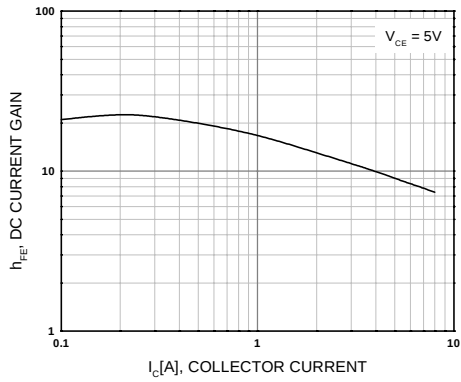


Figure 1. DC current Gain

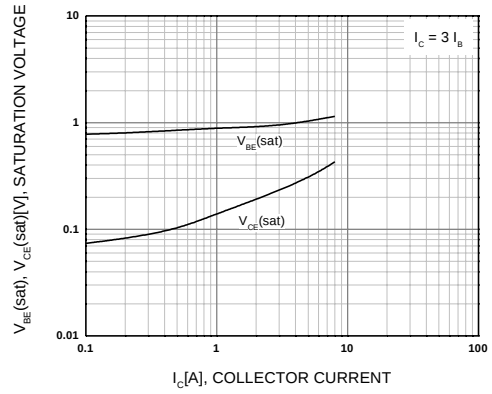


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

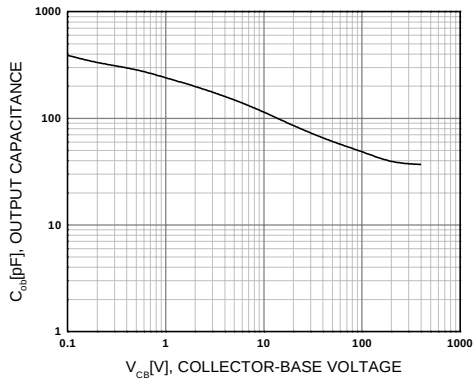


Figure 3. Collector Output Capacitance

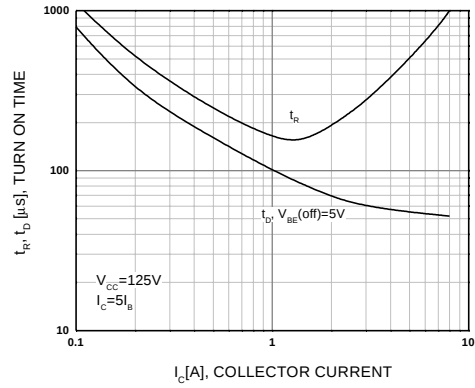


Figure 4. Turn On Time

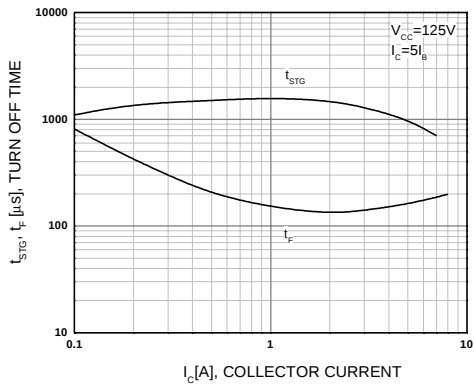


Figure 5. Turn Off Time

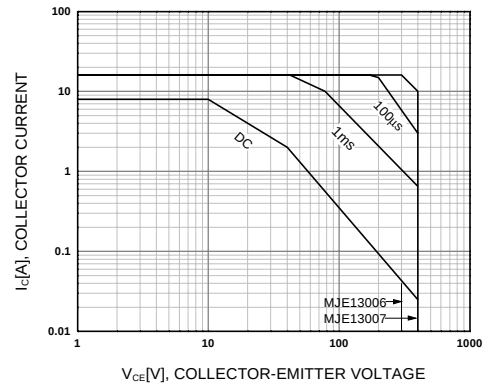


Figure 6. Safe Operating Area

Typical Characteristics (Continued)

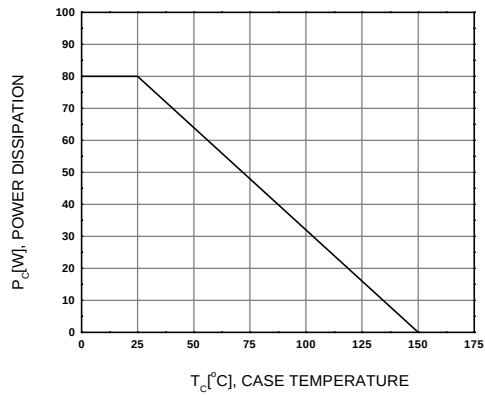


Figure 7. Power Derating

Technical drawing of a mechanical part, likely a connector or probe, showing front and top views with dimensions in millimeters.

Front View Dimensions:

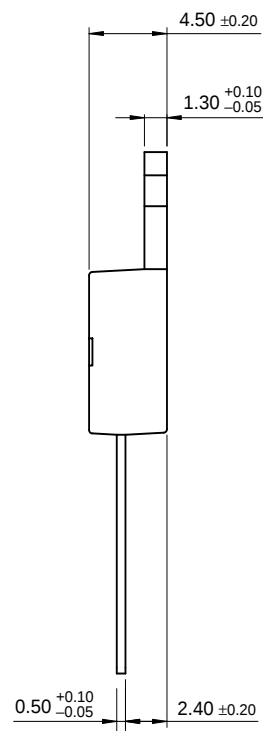
- Overall width: 9.90 ± 0.20
- Top width: (8.70)
- Hole diameter: $\varnothing 3.60 \pm 0.10$
- Top flange height: 1.30 ± 0.10
- Mounting hole diameter: 2.80 ± 0.10
- Main body height: 9.20 ± 0.20
- Internal feature height: (1.46)
- Pin height: 1.00
- Pin width: 1.27 ± 0.10
- Pin width: 1.52 ± 0.10
- Pin width: 0.80 ± 0.10
- Pin angle: 45°
- Pin length: 10.08 ± 0.30
- Overall height: 15.90 ± 0.20
- Maximum overall height: 18.95 MAX.

Top View Dimensions:

- Overall width: 10.00 ± 0.20

Material Specifications:

- 2.54 TYP
- $[2.54 \pm 0.20]$



Rev. A1, February 2001

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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